

Silicon TVS Diode

Features

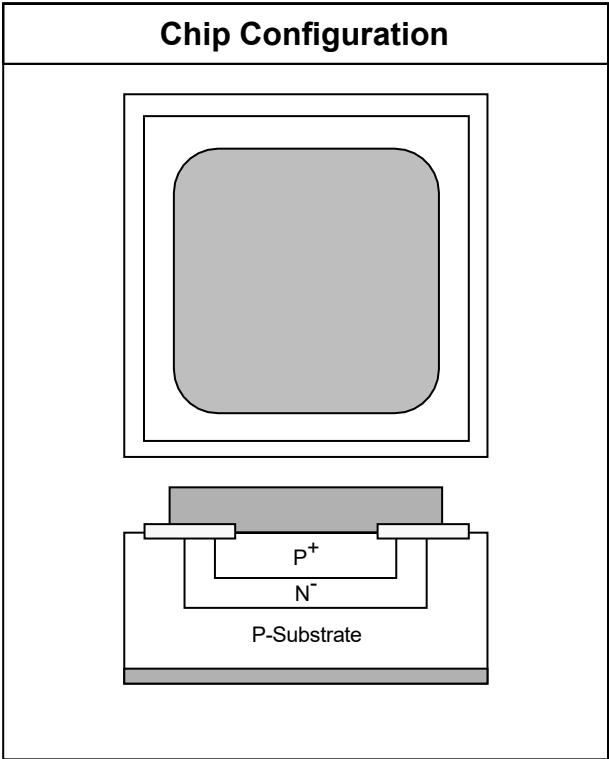
- ESD Protection
 - IEC 61000-4-2, Level 4
 - ±8kV (Contact Discharge), ±15kV (Air Discharge)
- Low Clamping Voltage, V_c
- Low Dynamic Resistance, R_{dyn} : 0.7ohm
- Low leakage current

Structure

- Bidirectional Vertical Structure
- Top electrode : Gold
- Bottom electrode : Gold

Size

- Chip size : 195(±20) μm x 195(±20) μm
- Thickness : 100(±20) μm
- Pad size : 140(±10) μm x 140(±10) μm



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	100	mW
ESD (IEC 61000-4-2, Contact)	V_{ESD}	± 8	kV
ESD (IEC 61000-4-2, Air)		±15	
Junction Temperature	T_j	150	C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R = 5\text{ mA}$	5.3	6.3	7.3	
Reverse Leakage Current	I_R	$V_{RWM} = 4\text{ V}$	-	-	0.1	μA
Forward Breakdown Voltage	V_{BF}	$I_R = 5\text{ mA}$	6.0	7.0	8.0	
Forward Leakage Current	I_F	$V_{FWM} = 4\text{ V}$	-	-	0.1	μA